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(54) Title: METHODS FOR FORMING A SILICON OXIDE LAYER OVER A SUBSTRATE

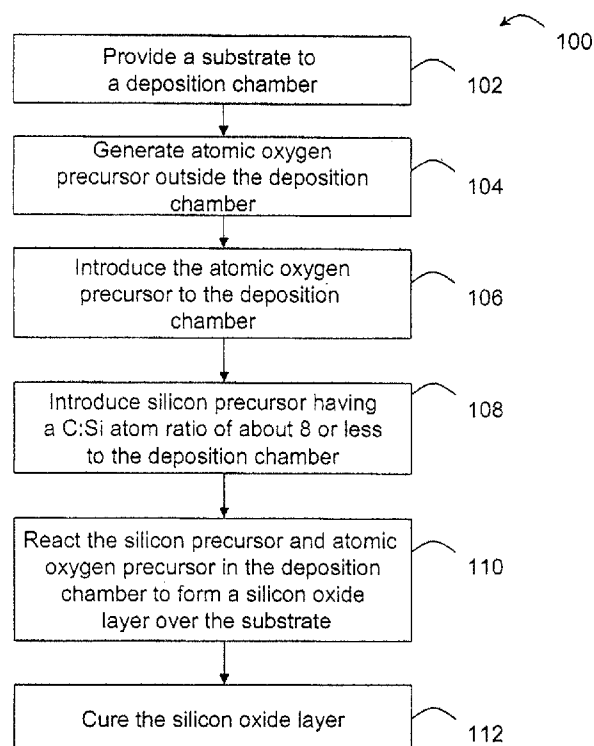


FIG. 1

(57) Abstract: A method of depositing a silicon oxide layer over a substrate includes providing a substrate to a deposition chamber. A first silicon-containing precursor, a second silicon-containing precursor and a NH_3 plasma are reacted to form a silicon oxide layer. The first silicon-containing precursor includes at least one of Si-H bond and Si-Si bond. The second silicon-containing precursor includes at least one Si-N bond. The deposited silicon oxide layer is annealed.



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